

<b>SANYO</b>	No.1289C	<b>2SA1347/2SC3401</b>
		PNP/NPN Epitaxial Planar Silicon Transistors <b>Switching Applications</b> (with Bias Resistance)

**Applications**

Switching circuit, inverter, interface circuit, driver

**Features**

- Built-in bias resistor (R1=46kΩ, R2=23kΩ).
- Small-sized package (SPA).

( ): 2SA1347

**Absolute Maximum Ratings/T<sub>a</sub>=25°C**

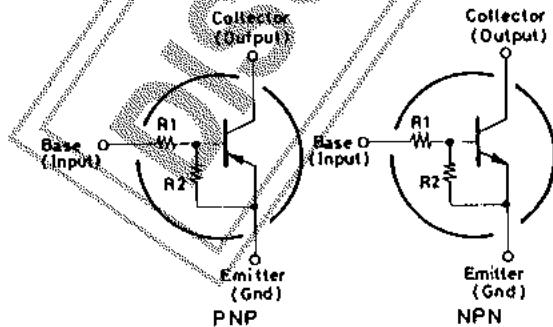
			unit
Collector to Base Voltage	V <sub>CB0</sub>	(-)150	V
Collector to Emitter Voltage	V <sub>CEO</sub>	(-)150	V
Emitter to Base Voltage	V <sub>EB0</sub>	(-)10	V
Collector Current	I <sub>C</sub>	(-)100	mA
Collector Current(Pulse)	I <sub>CP</sub>	(-)200	mA
Collector Dissipation	P <sub>C</sub>	300	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

**Electrical Characteristics/T<sub>a</sub>=25°C**

			min	typ	max	unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> =(-)140V, I <sub>E</sub> =0			(-)0.1	μA
Collector Cutoff Current	I <sub>CEO</sub>	V <sub>CE</sub> =(-)140V, I <sub>B</sub> =0			(-)0.5	μA
Emitter Cutoff Current	I <sub>EB0</sub>	V <sub>EB</sub> =(-)15V, I <sub>C</sub> =0	(-)140	(-)172	(-)100	μA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =(-)15V, I <sub>C</sub> =(-)5mA	50			
Gain-bandwidth product	f <sub>T</sub>	V <sub>CE</sub> =(-)10V, I <sub>C</sub> =(-)5mA		250 (200)		MHz
Output Capacitance	c <sub>ob</sub>	V <sub>CB</sub> =(-)10V, f=1MHz		3.7 (5.5)		pF
Collector to Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =(-)5mA, I <sub>B</sub> =(-)0.25mA	(-)0.1	(-)0.3		V

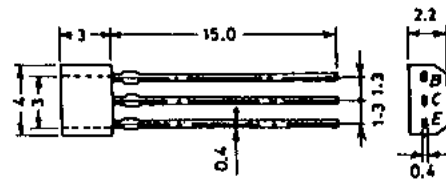
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**Electrical Connection**



**Case Outline 2033**

(unit: mm)



B: Base  
C: Collector  
E: Emitter  
SANYO: SPA

Specifications and information herein are subject to change without notice.

**SANYO Electric Co., Ltd. Semiconductor Business Headquarters**  
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito ku, TOKYO, 110 JAPAN

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			min	typ	max	unit
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu A, I_E = 0$	(-)50			V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)100\mu A, R_{BE} = \infty$	(-)50			V
Input Off Voltage	$V_{I(off)}$	$V_{CE} = (-)5V, I_C = (-)100\mu A$	(-)1.2	(-)1.6	(-)2.3	V
Input On Voltage	$V_{I(on)}$	$V_{CE} = (-)0.2V, I_C = (-)5mA$	(-)1.5	(-)3.1	(-)6.0	V
Input Resistance	$R_1$		32	46	60	k $\Omega$
Input Resistance Ratio	$R_1/R_2$		1.8	2.0	2.2	-

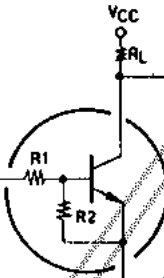
■ Sample Application Circuit

Input ON-state voltage: 6V or more

Input OFF-state voltage: 1.2V or less



INPUT



(For PNP, the polarity is reversed.)

